# Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low  $V_F = 0.50 \text{ V}$  at  $I_F = 5 \text{ A}$ 

#### **Features**

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

## **Typical Applications**

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

## **Mechanical Characteristics**

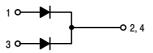
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec



## ON Semiconductor®

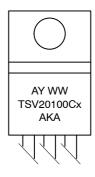
http://onsemi.com

## **PIN CONNECTIONS**





### **MARKING DIAGRAMS**



A = Assembly Location

Y = Year WW = Work Week

AKA = Polarity Designator

x = G or H

G = Pb-Free Package H = Halide-Free Package

## **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

### **MAXIMUM RATINGS**

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	100	V
Average Rectified Forward Current (Rated $V_R$ , $T_C = 130^{\circ}C$ )	Per device Per diode	I <sub>F(AV)</sub>	20 10	А
Peak Repetitive Forward Current (Rated V <sub>R</sub> , Square Wave, 20 kHz, T <sub>C</sub> = 125°C)	Per device Per diode	I <sub>FRM</sub>	40 20	Α
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I <sub>FSM</sub>	100	А
Operating Junction Temperature		TJ	-40 to +150	°C
Storage Temperature		T <sub>stg</sub>	-40 to +150	°C
Voltage Rate of Change (Rated V <sub>R</sub> )		dv/dt	10,000	V/μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### THERMAL CHARACTERISTICS

Rating		Symbol	Value	Unit
Maximum Thermal Resistance	Junction-to-Case Junction-to-Ambient	$R_{ hetaJC} \ R_{ hetaJA}$	2.0 70	°C/W

## **ELECTRICAL CHARACTERISTICS** (Per Leg unless otherwise noted)

Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1)	٧ <sub>F</sub>			V
$(I_F = 5 \text{ A}, T_J = 25^{\circ}\text{C})$ $(I_F = 10 \text{ A}, T_J = 25^{\circ}\text{C})$		0.55 0.65	- 0.98	
(IF = 10 A, IJ = 23 G)		0.03	0.96	
$(I_F = 5 \text{ A}, T_J = 125^{\circ}\text{C})$		0.50	_	
(I <sub>F</sub> = 10 A, T <sub>J</sub> = 125°C)		0.58	0.82	
Maximum Instantaneous Reverse Current (Note 1)	I <sub>R</sub>			
$(V_R = 70 \text{ V}, T_J = 25^{\circ}\text{C})$ $(V_R = 70 \text{ V}, T_J = 125^{\circ}\text{C})$		17 5.3	_	μA mA
(VH = 70 V, 1J = 123 O)		5.5	_	111/4
(Rated dc Voltage, T <sub>J</sub> = 25°C)		-	800	μΑ
(Rated dc Voltage, T <sub>J</sub> = 125°C)		12	25	mA

<sup>1.</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\leq 2.0\%$ 

## **ORDERING INFORMATION**

Device	Package	Shipping
NTSV20100CTG	TO-220AB (Pb-Free)	50 Units / Rail

#### TYPICAL CHARACTERISITICS

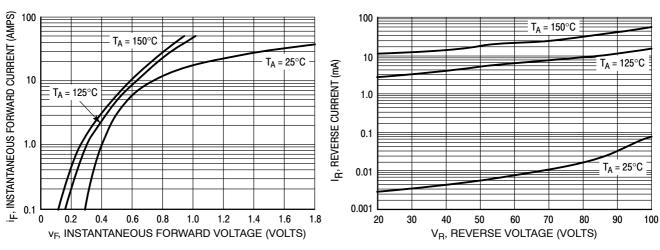


Figure 1. Typical Forward Voltage

Figure 2. Typical Reverse Current

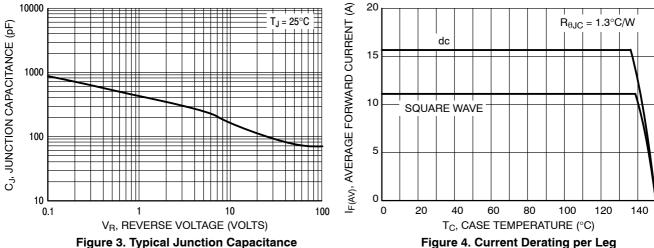


Figure 3. Typical Junction Capacitance

 $R_{\theta JC} = 1.3^{\circ}C/W$ 

40

35

30

25

20

15 10 5

0

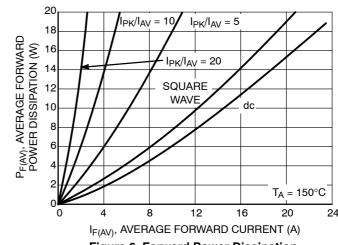
0

20

dc

**SQUARE WAVE** 

I<sub>E(AV)</sub>, AVERAGE FORWARD CURRENT (A)



T<sub>C</sub>, CASE TEMPERATURE (°C) Figure 5. Current Derating

Figure 6. Forward Power Dissipation

140

## **TYPICAL CHARACTERISITICS**

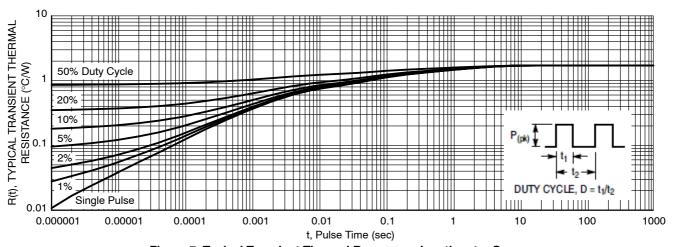
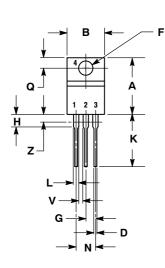
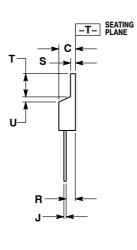


Figure 7. Typical Transient Thermal Response, Junction-to-Case

#### PACKAGE DIMENSIONS

TO-220 CASE 221A-09 ISSUE AF





#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 6:

PIN 1. ANODE

- CATHODE 2.
- ANODE CATHODE

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